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BSC152N10NSF G-VB Datasheet

N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
100	0.009 at V_{GS} = 10 V	65

FEATURES

- Trench Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- 100 % R_g Tested

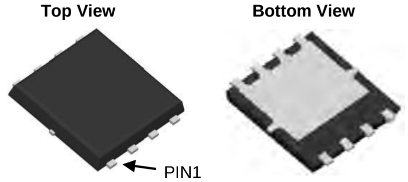
RoHS COMPLIANT

APPLICATIONS

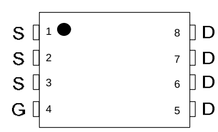
- Isolated DC/DC Converters

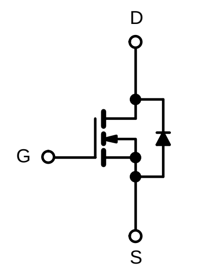
DFN5X6

Top View Bottom View



Top View





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	100	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current (T_J = 150 °C)	T_C = 25 °C	I_D	65	A
	T_C = 70 °C		60	
	T_A = 25 °C		20 [b, c]	
	T_A = 70 °C		18.5[b, c]	
Pulsed drain current (t = 100 μs)		I_{DM}	180	
Continuous source-drain diode current	T_C = 25 °C	I_S	60	
	T_A = 25 °C		4.8 [b, c]	
Single pulse avalanche current	L = 0.1 mH	I_{AS}	30	
Single pulse avalanche energy		E_{AS}	40	mJ
Maximum power dissipation	T_C = 25 °C	P_D	80	W
	T_C = 70 °C		50	
	T_A = 25 °C		5 [b, c]	
	T_A = 70 °C		3.2 [b, c]	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) [c]			260	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient [b]	t ≤ 10 s	R_{thJA}	20	25	°C/W
Maximum junction-to-case (drain)	Steady state	R_{thJC}	1.6	2	

Notes
a. Package limited
b. Surface mounted on 1" x 1" FR4 board
c. t = 10 s

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA	100	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	I_D = 10 mA	-	81	-	mV/°C
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$	I_D = 250 μA	-	-7.5	-	
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250 μA	3	-	5	V
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V	-	-	1	μA
		V_{DS} = 100 V, V_{GS} = 0 V, T_J = 70 °C	-	-	15	
On-state drain current [a]	$I_{D(on)}$	$V_{DS} \geq$ 10 V, V_{GS} =10 V	40	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} =10 V, I_D = 10 A	-	0.009	-	Ω
		V_{GS} = 7.5 V, I_D = 10 A	-	0.012	-	
Forward transconductance [a]	g_{fs}	V_{DS} = 15 V, I_D = 10 A	-	46	-	S
Dynamic [b]						
Input capacitance	C_{iss}	V_{DS} = 50 V, V_{GS} = 0 V, f = 1 MHz	-	3970	-	pF
Output capacitance	C_{oss}		-	132	-	
Reverse transfer capacitance	C_{rss}		-	11.2	-	
Total gate charge	Q_g	V_{DS} = 50 V, V_{GS} = 10 V, I_D = 10 A	-	20		nC
		V_{DS} = 50 V, V_{GS} = 7.5 V, I_D = 10 A	-	15	-	
Gate-source charge	Q_{gs}		-	6.45	-	
Gate-drain charge	Q_{gd}		-	3.5	-	
Output charge	Q_{oss}	V_{DS} = 50 V, V_{GS} = 0 V	-	22	-	
Gate resistance	R_g	f = 1 MHz	0.2	0.76	1.4	Ω
Turn-on delay time	$t_{d(on)}$	V_{DD} = 50 V, R_L = 5 Ω, $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω	-	12	24	ns
Rise time	t_r		-	5	10	
Turn-off delay time	$t_{d(off)}$		-	19	38	
Fall time	t_f		-	5	10	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 50 V, R_L = 5 Ω, $I_D \cong$ 10 A, V_{GEN} = 7.5 V, R_g = 1 Ω	-	15	30	
Rise time	t_r		-	6	12	
Turn-off delay time	$t_{d(off)}$		-	19	38	
Fall time	t_f		-	5	10	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	T_C = 25 °C	-	-	60	A
Pulse diode forward current	I_{SM}		-	-	80	
Body diode voltage	V_{SD}	I_S = 5 A, V_{GS} = 0 V	-	0.78	1.1	V
Body diode reverse recovery time	t_{rr}	I_F = 10 A, di/dt = 100 A/μs, T_J = 25 °C	-	43	86	ns
Body diode reverse recovery charge	Q_{rr}		-	72	144	nC
Reverse recovery fall time	t_a		-	33	-	ns
Reverse recovery rise time	t_b		-	10	-	

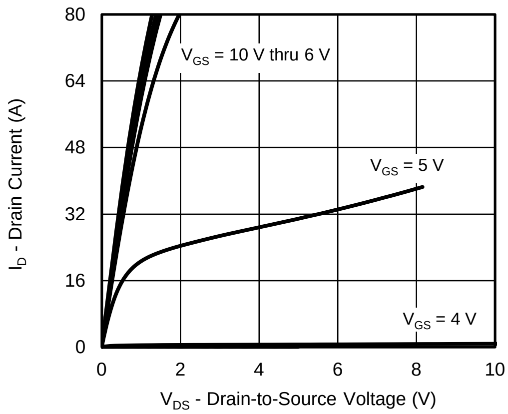
Notes

a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %

b. Guaranteed by design, not subject to production testing

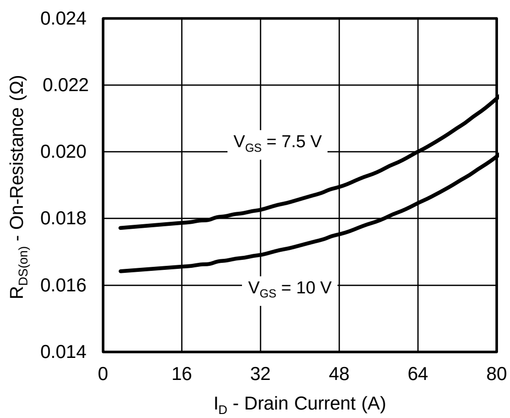
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



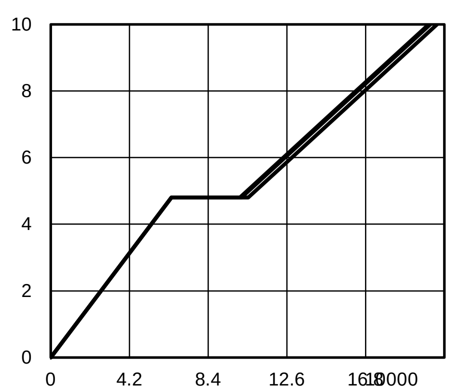
Output Characteristics

Transfer Characteristics



On-Resistance vs. Drain Current and Gate Voltage

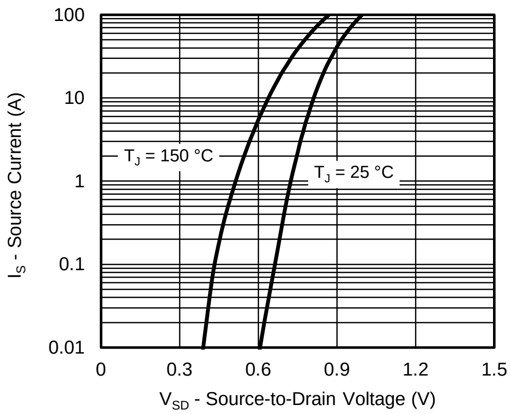
Capacitance



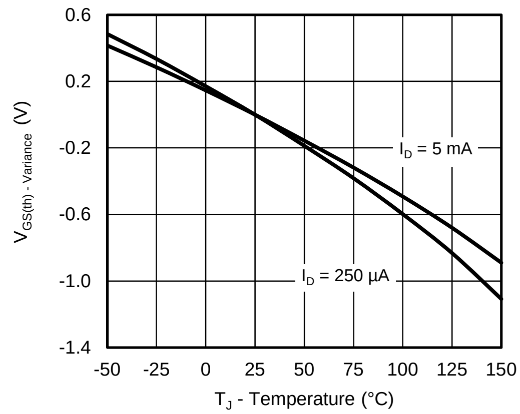
Gate Charge

On-Resistance vs. Junction Temperature

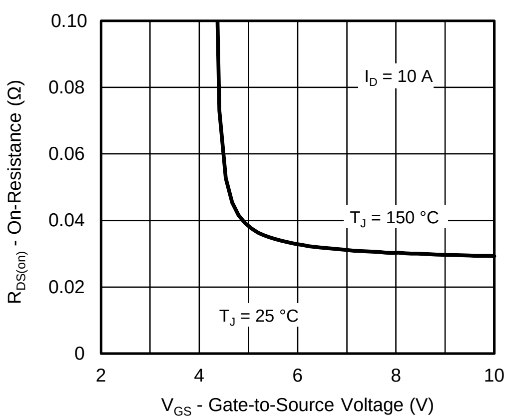
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



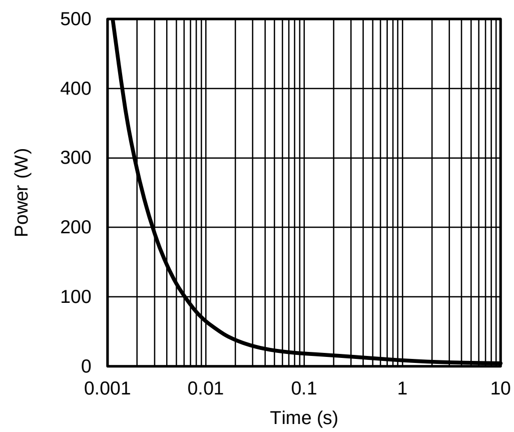
Source-Drain Diode Forward Voltage



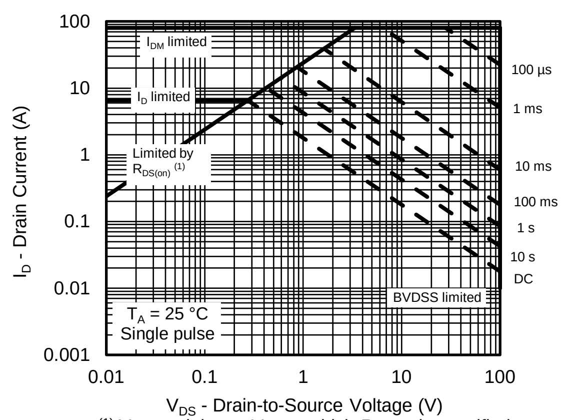
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



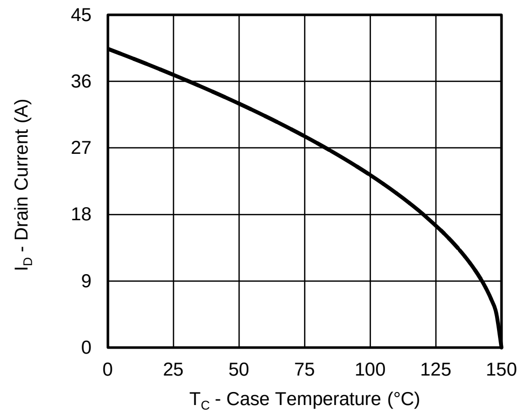
Single Pulse Power, Junction-to-Ambient



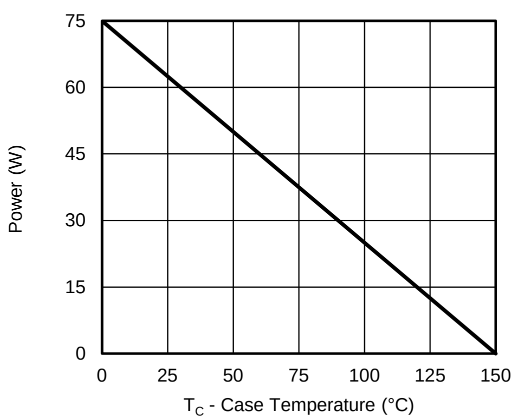
(1) V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

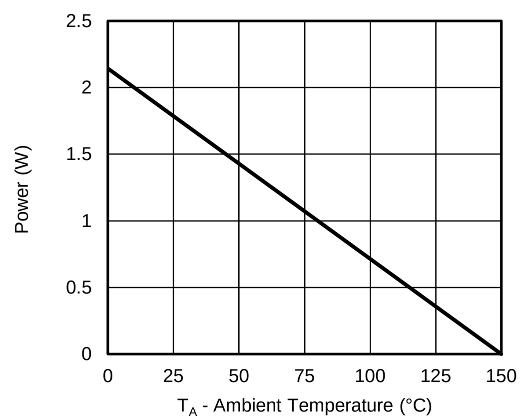
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating [a]



Power, Junction-to-Case

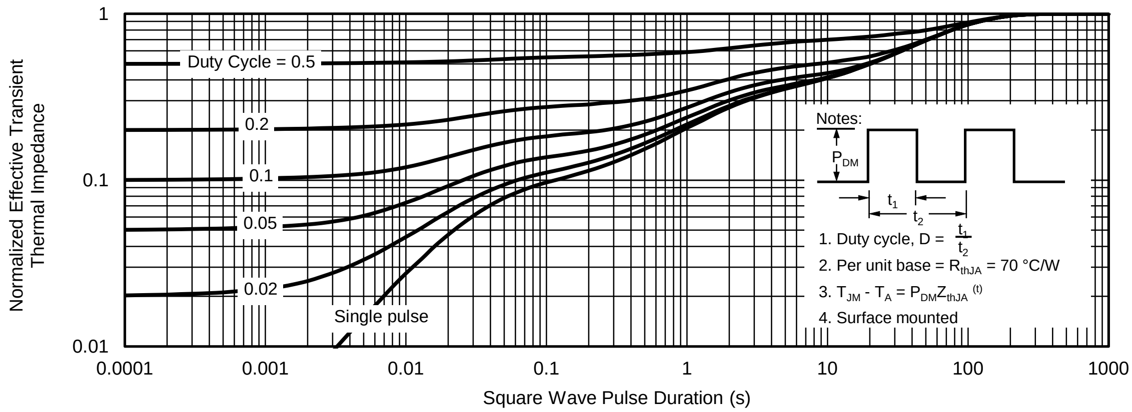


Power, Junction-to-Ambient

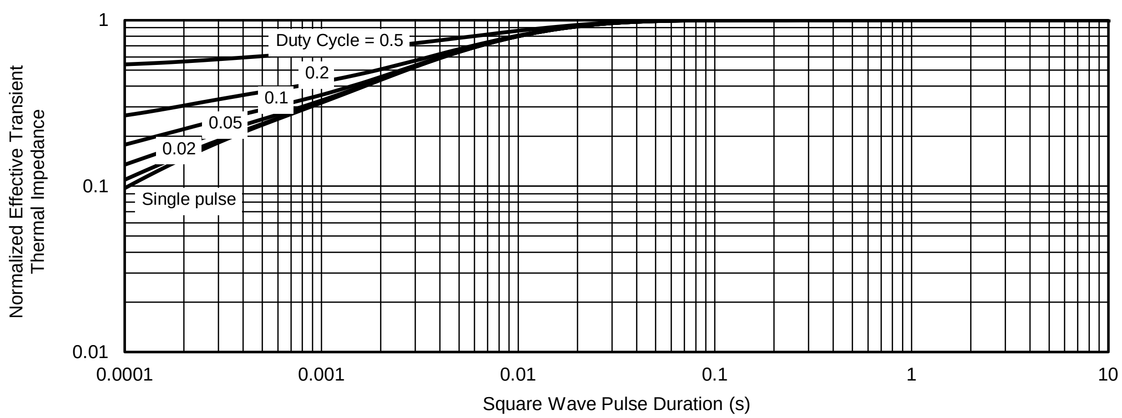
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

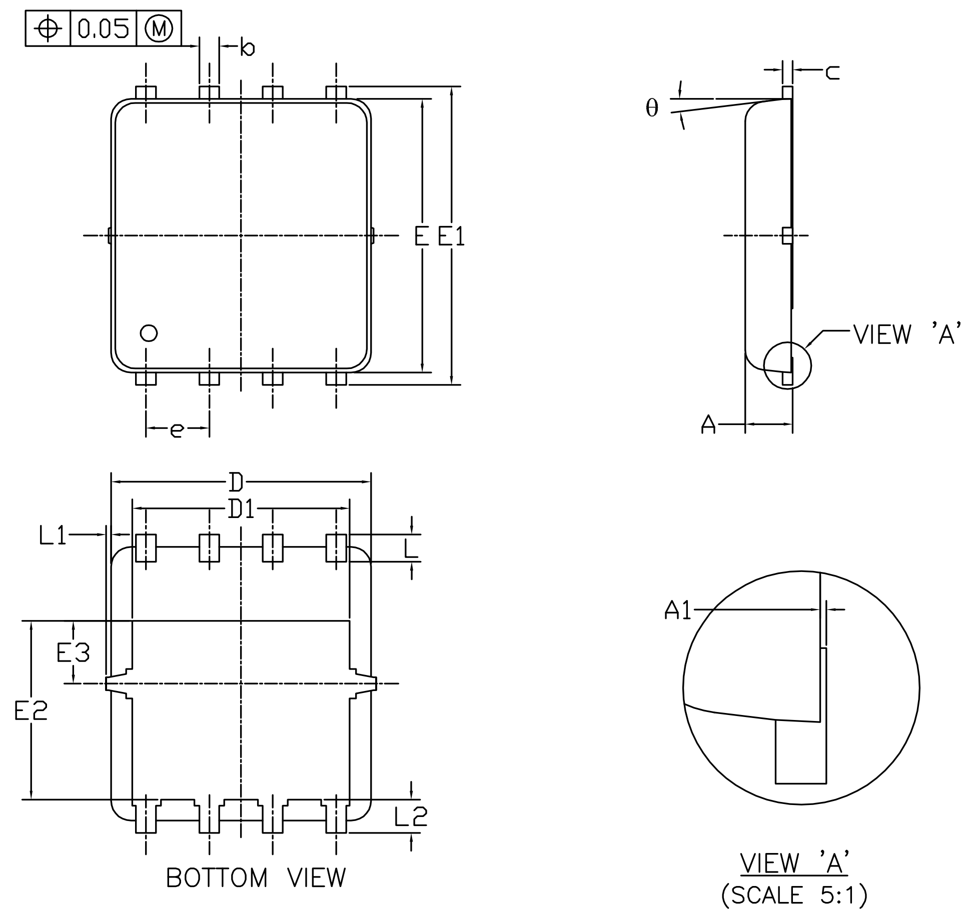


Normalized Thermal Transient Impedance, Junction-to-Ambient

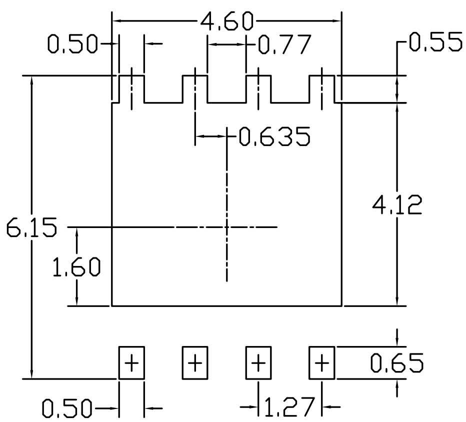


Normalized Thermal Transient Impedance, Junction-to-Case

DFN5x6_8L_EP1_P PACKAGE OUTLIN



RECOMMENDED LAND PATTERN



UNIT: mm

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.10	5.20	5.30	0.201	0.205	0.209
D1	4.25	4.35	4.45	0.167	0.171	0.175
E	5.45	5.55	5.65	0.215	0.219	0.222
E1	5.95	6.05	6.15	0.234	0.238	0.242
E2	3.525	3.625	3.725	0.139	0.143	0.147
E3	1.175	1.275	1.375	0.046	0.050	0.054
e		1.27 BSC			0.050 BSC	
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	---	0.15	0	---	0.006
L2		0.68 REF			0.027 REF	
θ	0°	---	10°	0°	---	10°

NOTE

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
   MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
2. CONTROLLING DIMENSION IS MILLIMETER.
   CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

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